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FIG. 1A

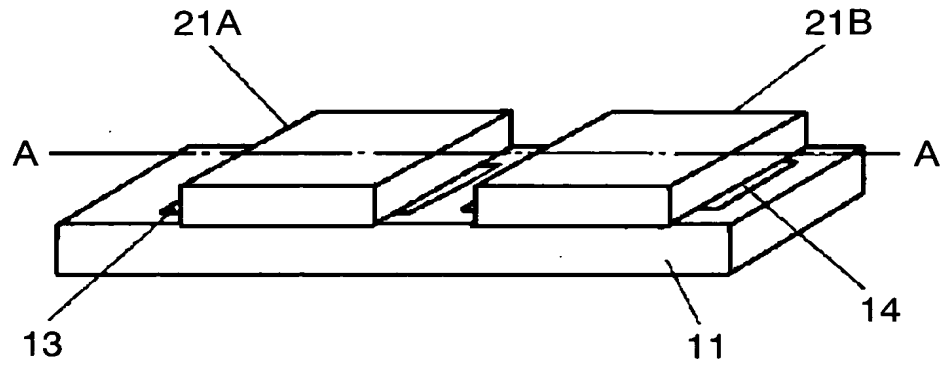
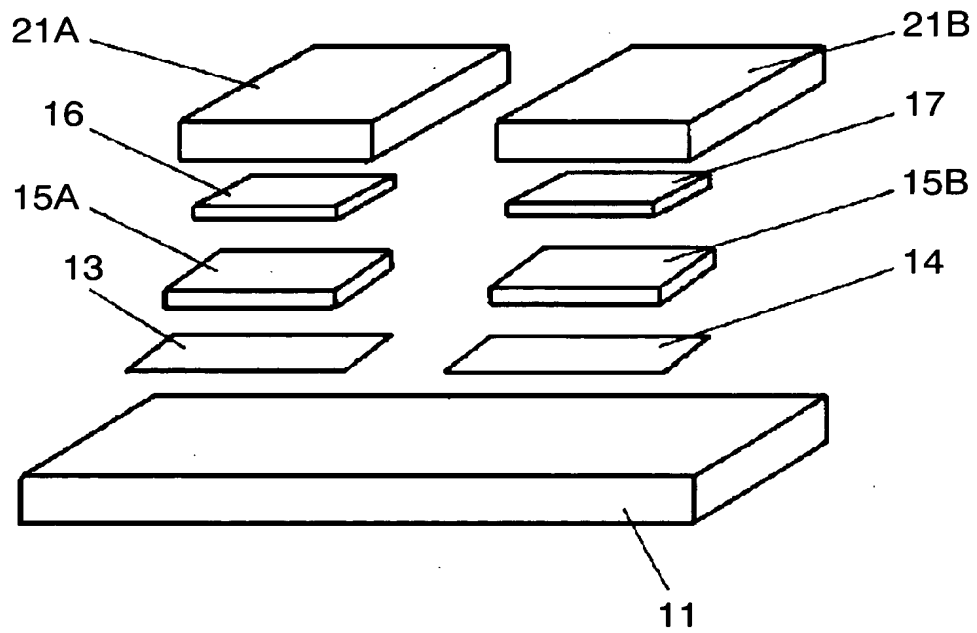


FIG. 1B



This cross-sectional diagram shows two semiconductor units, 15A and 15B, positioned on a common substrate 11. Unit 15A on the left consists of a base layer 13, a middle layer 16, and a top layer 21A. Unit 15B on the right consists of a base layer 21B, a middle layer 17, a top layer 14, and a protective layer 15B. The substrate 11 is indicated by a diagonal hatching pattern at the bottom.

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FIG. 4

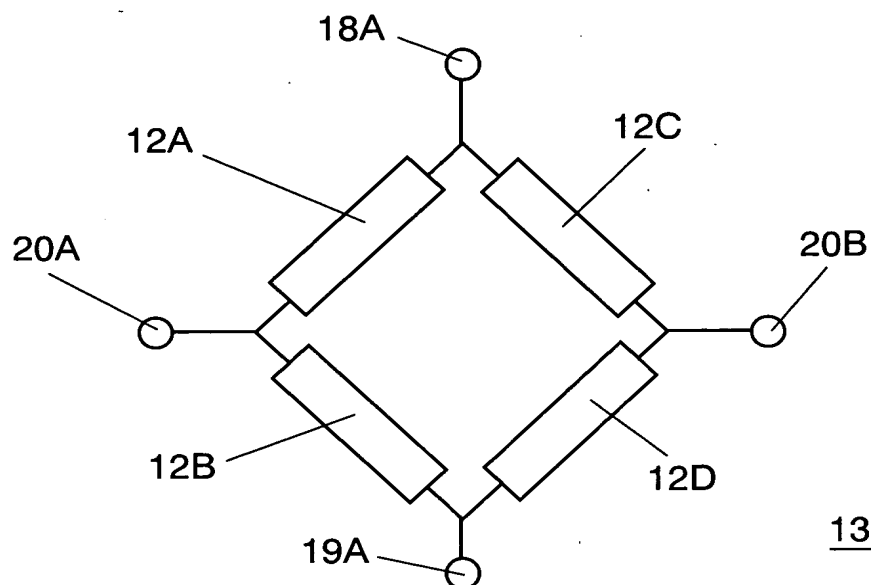
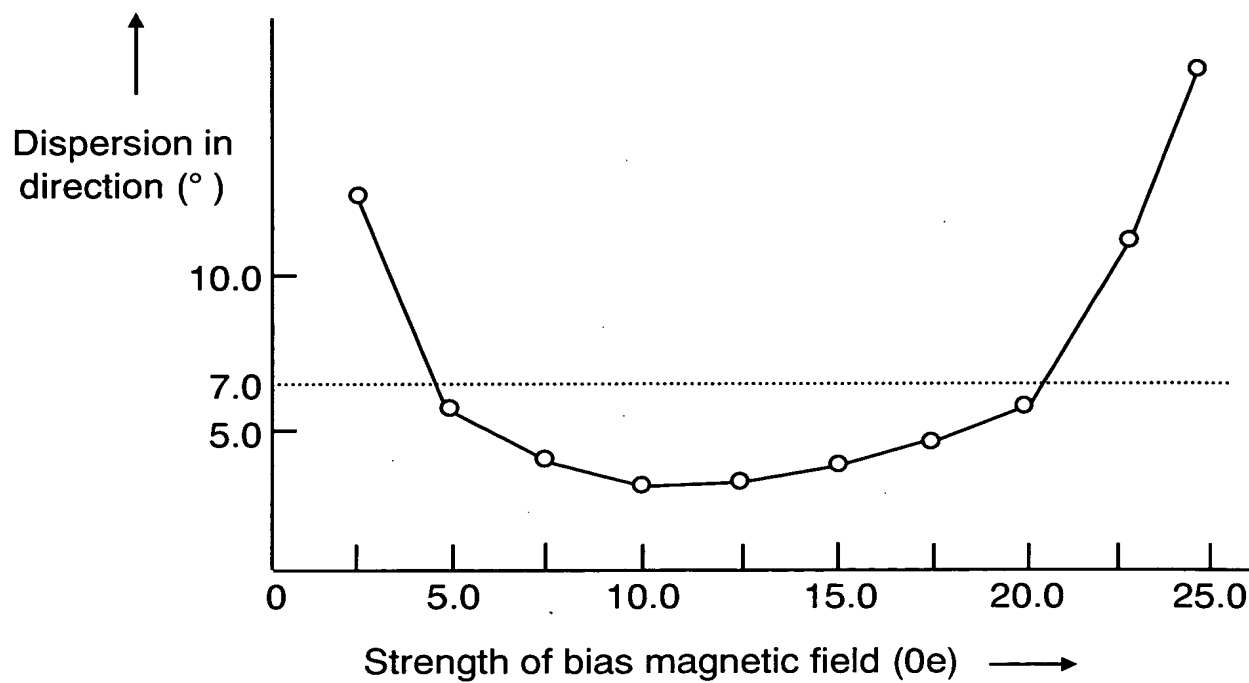


FIG. 5



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FIG. 6

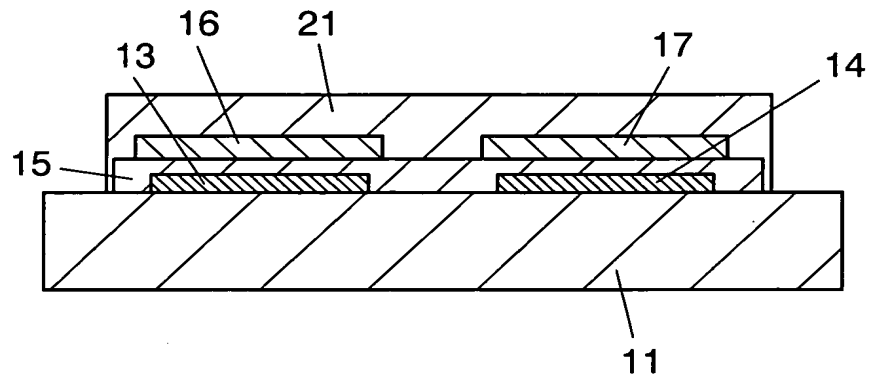
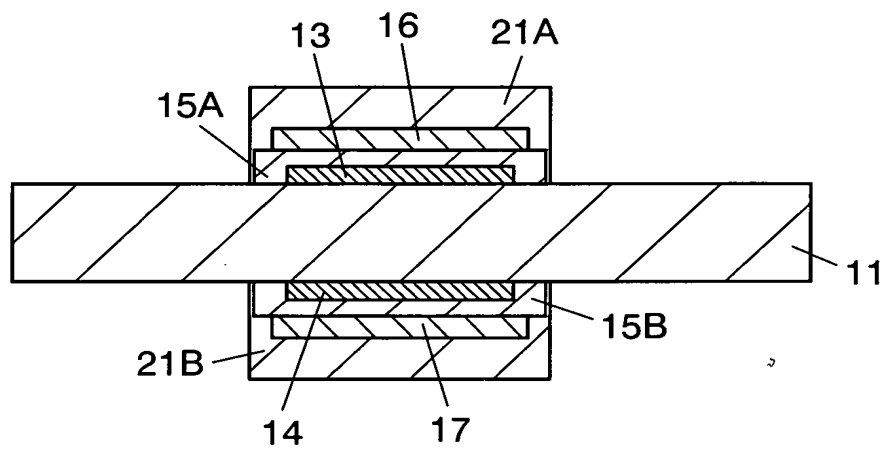


FIG. 7



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FIG. 8

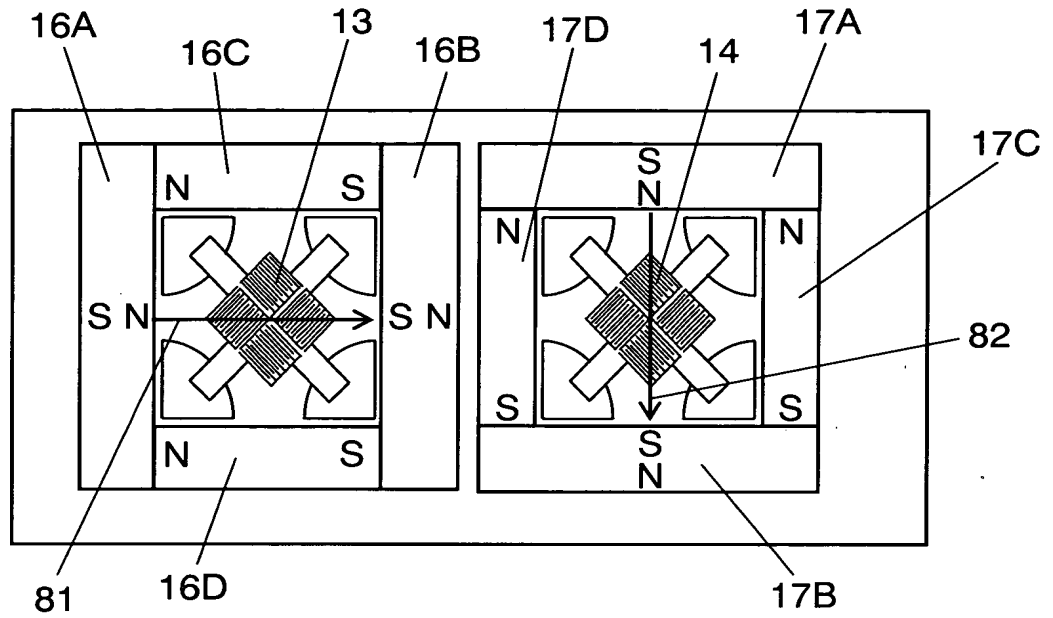
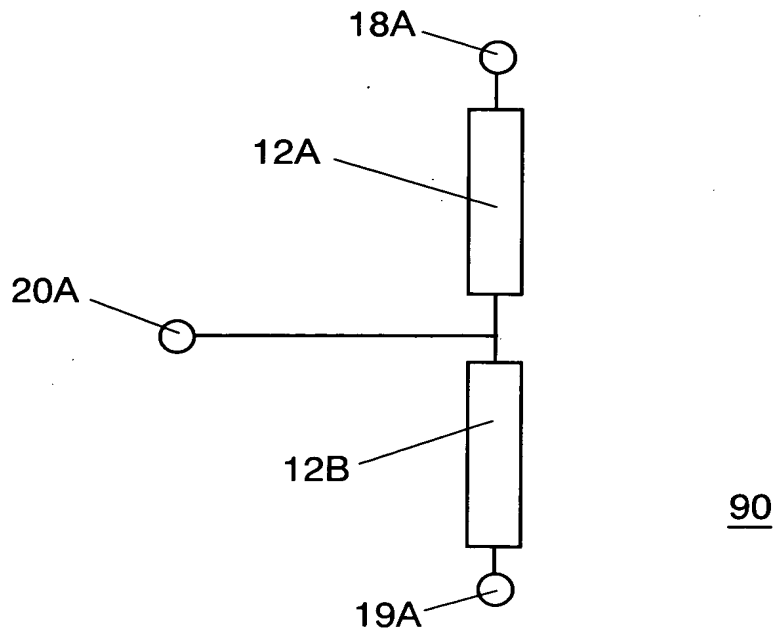


FIG. 9



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FIG. 10A

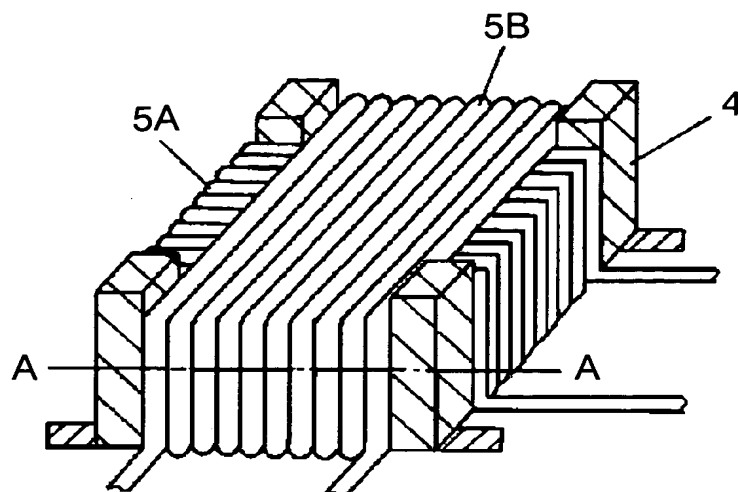
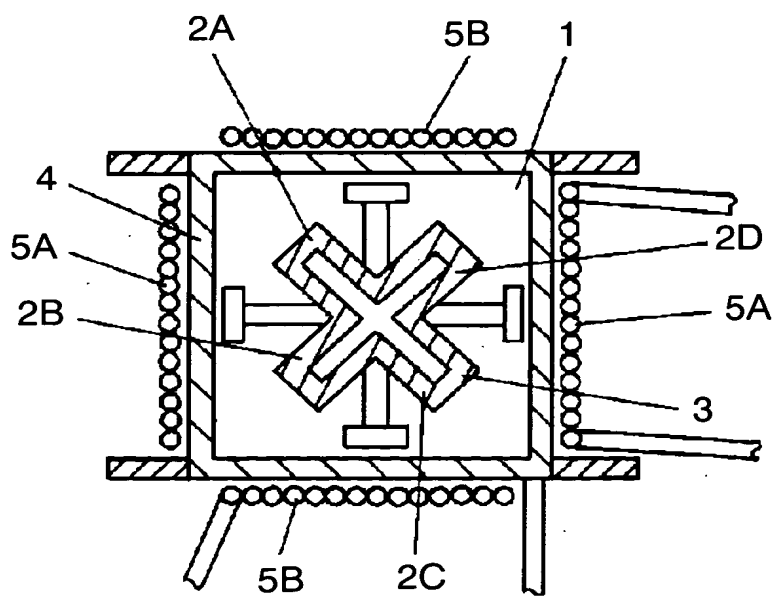


FIG. 10B



Reference marks in the drawings.

1. Substrate

2A, 2B, 2C, 2D. Detecting element

3. Bridge circuit

4. Holder

5A. First coil

5B. Second coil

11. Substrate

12A. First detecting element

12B. Second detecting element

12C. Third detecting element

12D. Fourth detecting element

12E. Fifth detecting element

12F. Sixth detecting element

12G. Seventh detecting element

12H. Eighth detecting element

13. First bridge circuit

14. Second bridge circuit

15, 15A, 15B. Insulating layer

16. First magnetic bias application part

16A, 16B, 16C, 16D. Magnetic bias application part

17. Second magnetic bias application part

17A, 17B, 17C, 17D. Magnetic bias application part

18A, 18B. Input electrode

19A, 19B. Ground electrode

20A. First output electrode

20B/ Second output electrode

20C. Third output electrode

20D. Fourth output electrode

21, 21A, 21B. Cover layer

31, 81. Magnetic field direction of first magnetic bias application part

32, 82. Magnetic field direction of second magnetic bias application part

90. First detecting circuit